

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions and listings of claims in the application:

**Listing of Claims:**

Claims 1-18 (Canceled)

19. (Currently Amended) A semiconductor device comprising:

a semiconductor substrate;

a conductive plug formed on the semiconductor substrate;

a lower electrode formed in contact with the conductive plug and having a side and upper surface, a surface area of the side being larger than a surface area of the upper surface, the lower electrode comprising a plurality of crystal grains, the crystal grains containing a metallic element;

a capacitor insulating film formed on a side of the lower electrode; and

an upper electrode formed above the lower electrode via the capacitor insulating film,

the capacitor insulating film being formed above a top surface of the lower electrode via a second insulating film different from the capacitor insulating film, and

a grain boundary between adjacent two of said plurality of crystal grains ~~comprising~~ of the lower electrode being substantially perpendicular to an interface between the lower electrode and the capacitor insulating film.

Claim 20-30 (Canceled)